

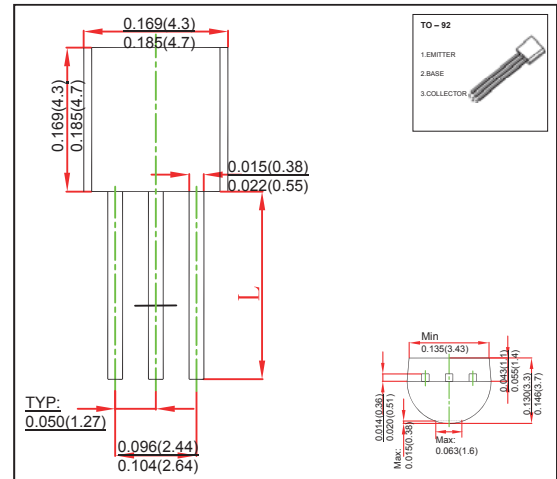
TO-92 Plastic-Encapsulate Transistors

FEATURES

- Switching and amplification in high voltage
- Applications such as telephony
- Low current
- High voltage
- PNP Transistors

MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.6	A
Collector Power Dissipation	K_D	625	mW
Thermal Resistance, junction to Ambient	R_{KJA}	200	°C /W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~+150	°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.1mA, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	
DC current gain	h_{FE}	$V_{CE} = -1V, I_C = -1mA$	30			
		$V_{CE} = -1V, I_C = -10mA$	50			
		$V_{CE} = -2V, I_C = -150mA$	50		150	
		$V_{CE} = -2V, I_C = -500mA$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -150mA, I_B = -15mA$			-0.4	V
		$I_C = -500mA, I_B = -50mA$			-0.75	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -150mA, I_B = -15mA$	-0.75		-0.95	V
		$I_C = -500mA, I_B = -50mA$			-1.3	V
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			8.5	pF
Emitter input capacitance	C_{ib}	$V_{EB} = -0.5V, I_C = 0, f = 1MHz$			30	pF
Transition frequency	f_T	$V_{CE} = -10V, I_C = -20mA, f = 100MHz$	150			MHz

*Pulse test: pulse width $\leq 300\mu s$, duty cycles $\leq 2.0\%$.